N-Ch and P-Ch Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

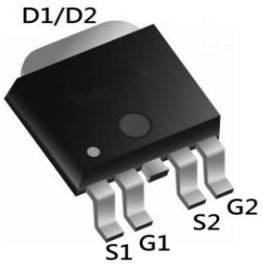
Green

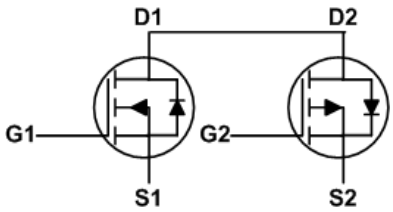
BVDSS	RDSON	ID
60V	23mΩ	30A
-60V	31 mΩ	-30A

Description

The XR6030 is the high performance complementary N-ch and P-ch MOSFETs with high cell density, whichprovide excellent RDSON and gate charge for most of the synchronous buck converter applications . The XR6030 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

TO252-4L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	60	-60	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	30	-30	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	13	-15	A
I_{DM}	Pulsed Drain Current[2]	100	-120	A
EAS	Single Pulse Avalanche Energy[3]	39	---	mJ
I_{AS}	Avalanche Current	14	---	A
P_D@T_C=25℃	Total Power Dissipation[4]	41.7	89	W
T_{STG}	Storage Temperature Range	-55 to 175	-55 to 175	℃
T_J	Operating Junction Temperature Range	-55 to 175	-55 to 175	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	3	℃/W

N-Channel Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=10A	---	23	32	mΩ
		V_{GS}=4.5V , I_D=5A	---	31.5	40	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.7	2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=60V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=60V , V_{GS}=0V , T_J=55℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=10A	---	15.5	---	S
Q_g	Total Gate Charge (10V)	V_{DS}=30V , V_{GS}=10V , I_D=10A	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	4.2	---	
Q_{gd}	Gate-Drain Charge		---	6.9	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3Ω I_D=10A	---	6.4	---	ns
T_r	Rise Time		---	15.3	---	
$T_{d(off)}$	Turn-Off Delay Time		---	25	---	
T_f	Fall Time		---	7.6	---	
C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , f=1MHz	---	1355	---	pF
C_{oss}	Output Capacitance		---	60	---	
C_{rss}	Reverse Transfer Capacitance		---	49	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	30	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=10A , T_J=25℃	---	---	1.2	V

Note :

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C
2. The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.4mH, I_{AS}=14A
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

P-Channel Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	---	---	V/ ℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-3A	---	31	38	mΩ
		V_{GS}=-4.5V , I_D=-2A	---	40	50	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.3	-1.7	-2.3	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-60V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-60V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-3A	---	---	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	13	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-30V , V_{GS}=-10V , I_D=-10A	---	13.4	---	nC
Q_{gs}	Gate-Source Charge		---	3.35	---	
Q_{gd}	Gate-Drain Charge		---	1.82	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-30V , V_{GS}=-10V , R_G=5.0Ω, I_D=-10A	---	10	---	ns
T_r	Rise Time		---	6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	23	---	
T_f	Fall Time		---	11	---	
C_{iss}	Input Capacitance	V_{DS}=-30V , V_{GS}=0V , f=1MHz	---	862	---	pF
C_{oss}	Output Capacitance		---	163	---	
C_{rss}	Reverse Transfer Capacitance		---	8	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-30	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	IF=-10A , di/dt=100A/μs , T_J=25℃	---	18	---	nS
Q_{rr}	Reverse Recovery Charge		---	27	---	nC

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-30V,V_{GS}=-10V,L=1mH
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

N-Channel Typical Characteristics

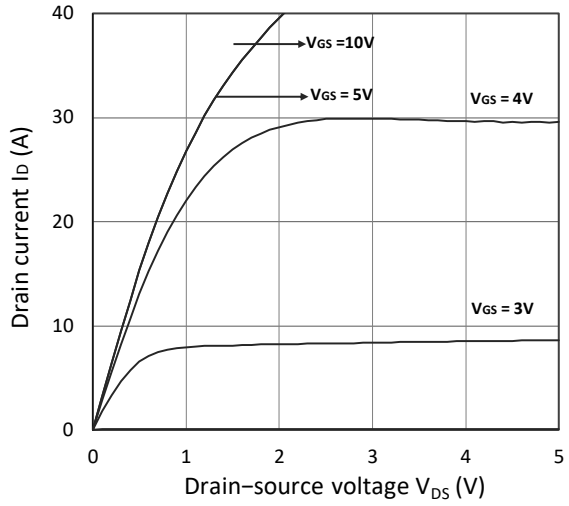


Figure 1. Output Characteristics

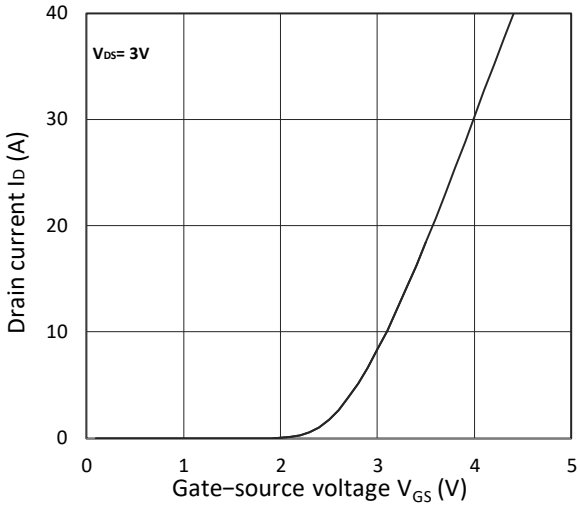


Figure 2. Transfer Characteristics

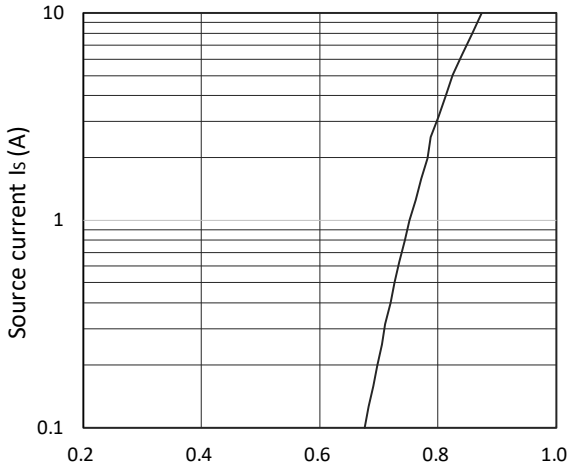


Figure 3. Forward Characteristics of Reverse

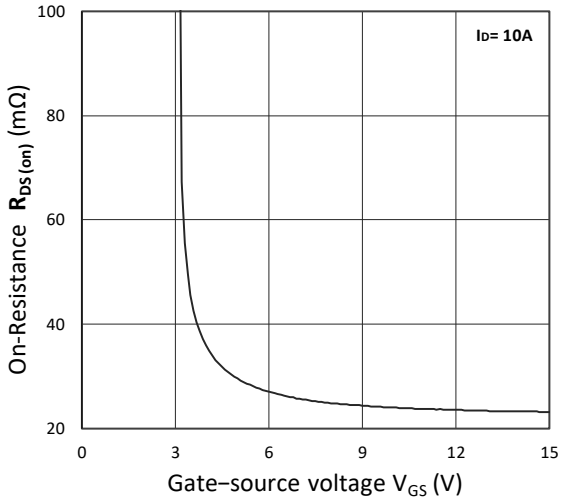


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

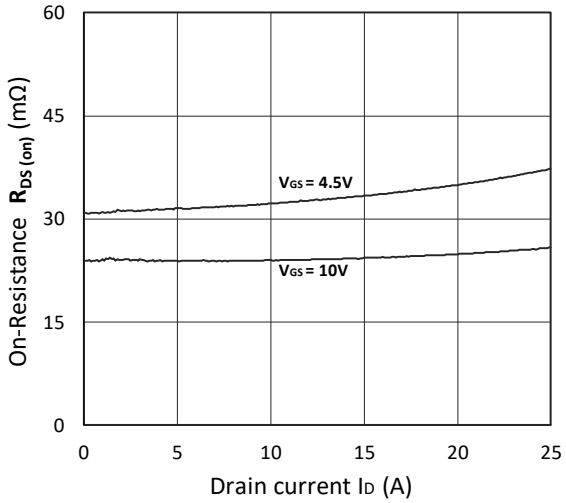


Figure 5. $R_{DS(ON)}$ vs. I_D

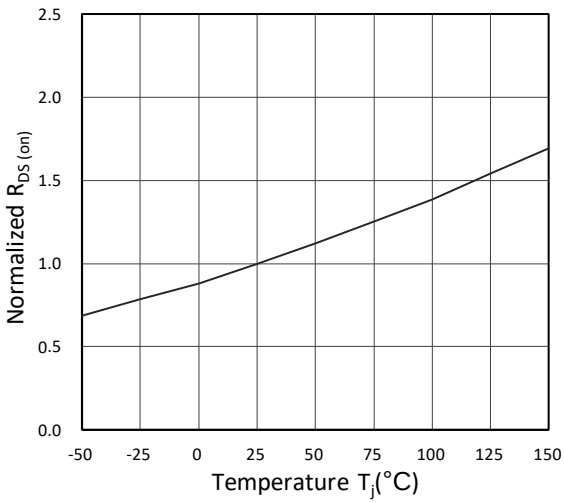


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

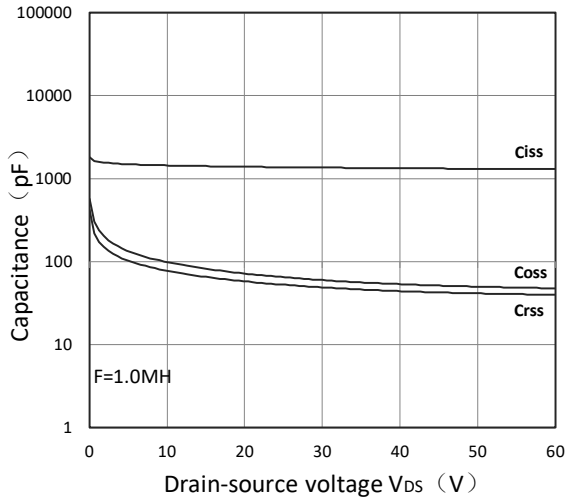


Figure 7. Capacitance Characteristics

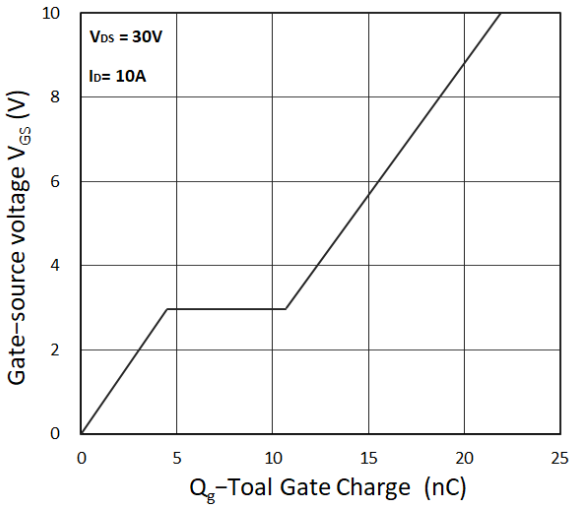


Figure 8. Gate Charge Characteristics

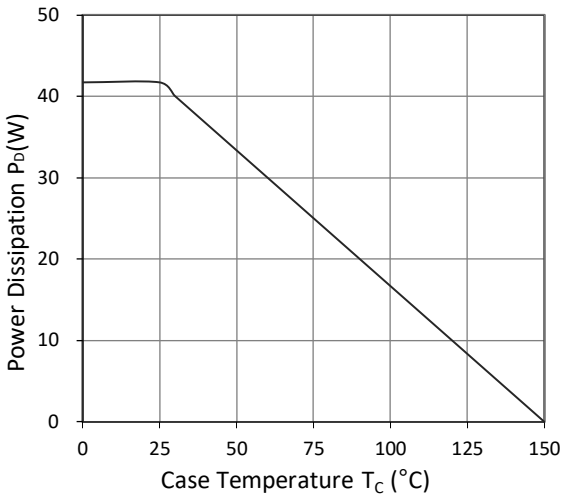


Figure 9. Power Dissipation

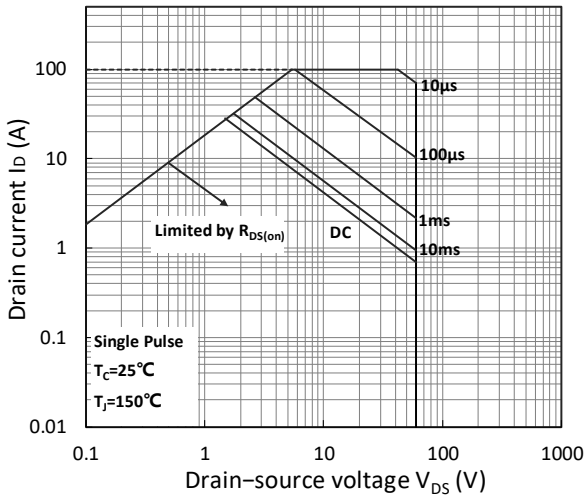


Figure10. Safe Operating Area

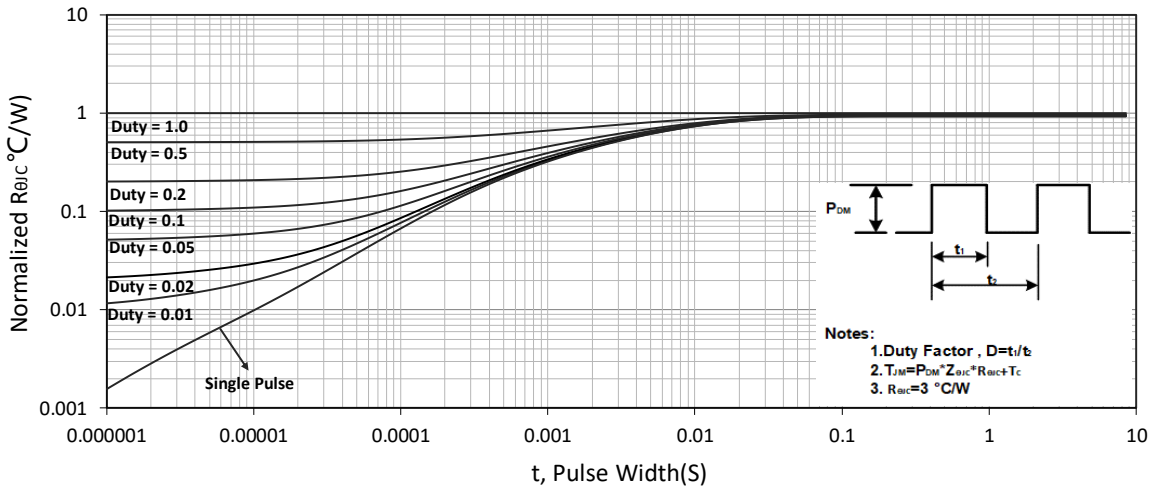
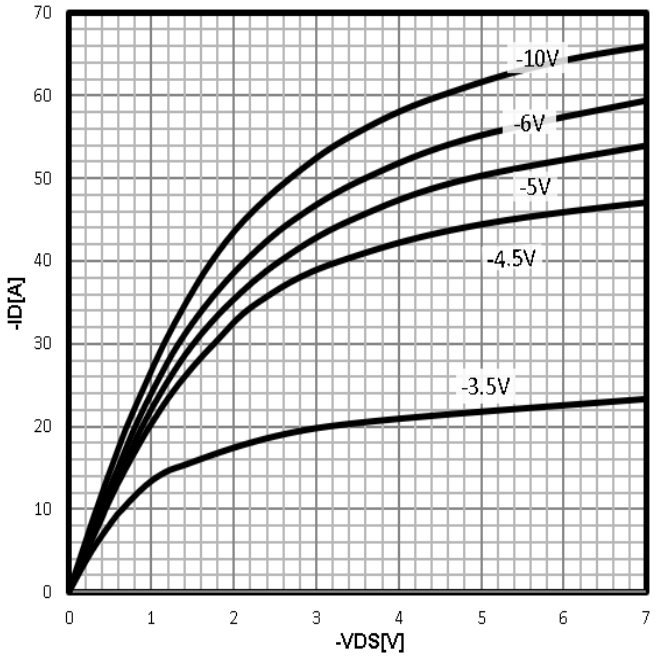


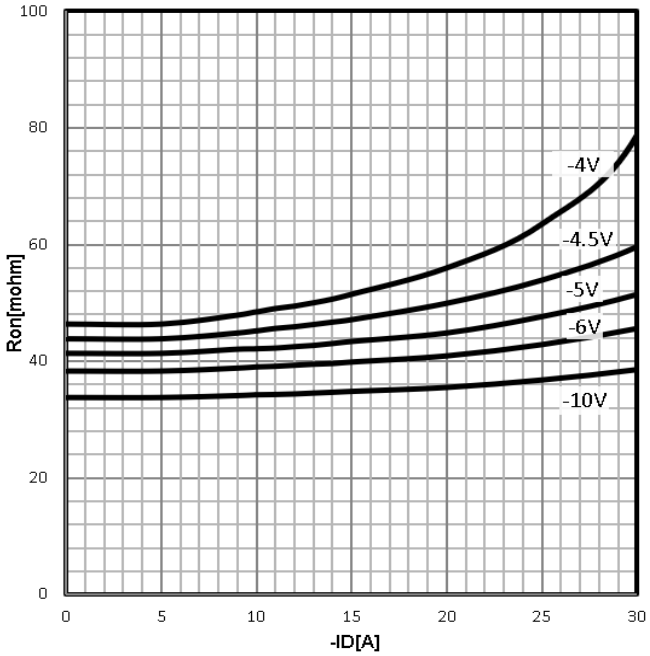
Figure 11. Normalized Maximum Transient Thermal Impedance

P-Channel Typical Characteristics

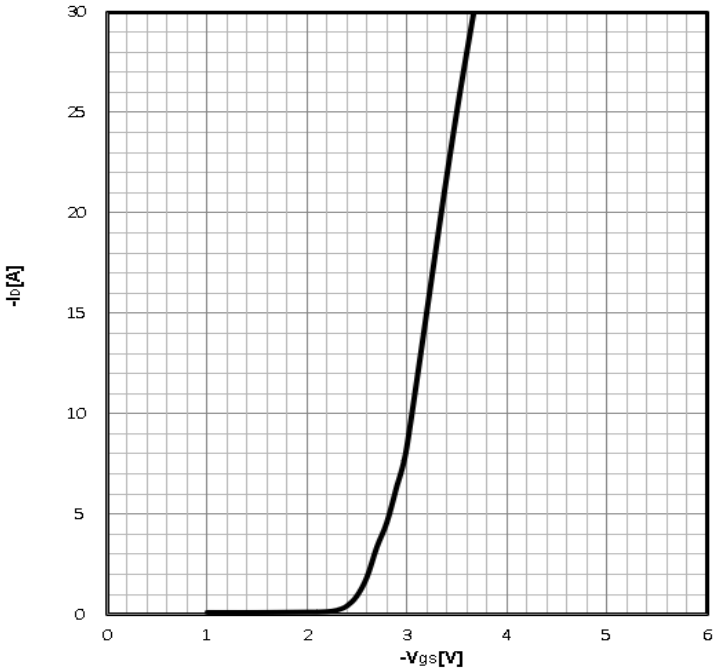
Typ. output characteristics
$-I_D=f(-V_{DS})$



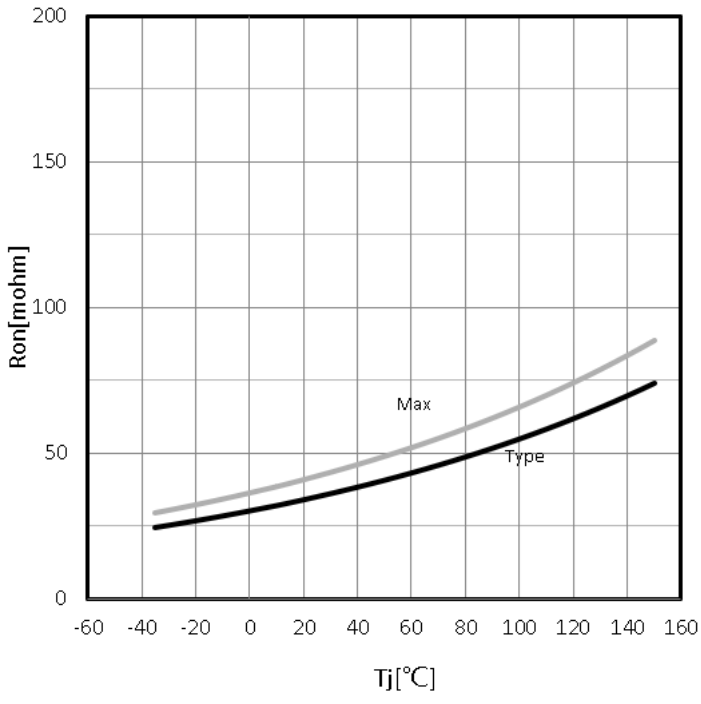
Typ. drain-source on resistance $R_{DS(on)}=f(-I_D)$



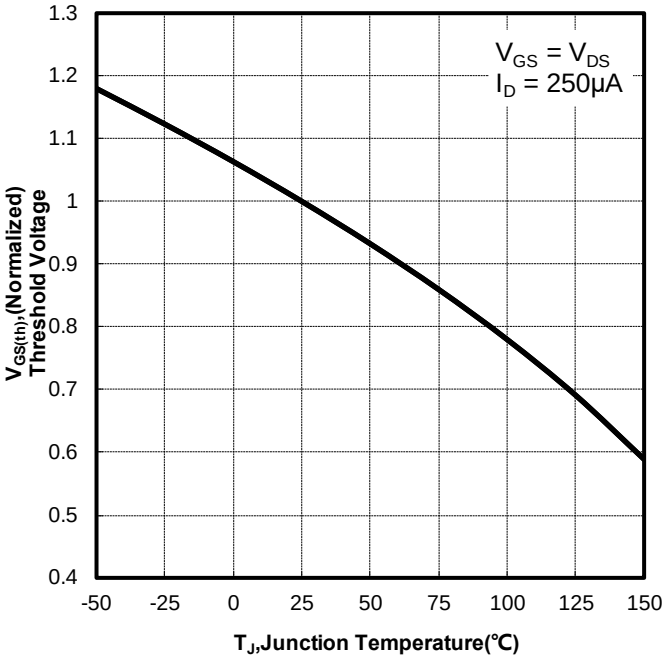
Typ. transfer characteristics
$-I_D=f(-V_{GS})$



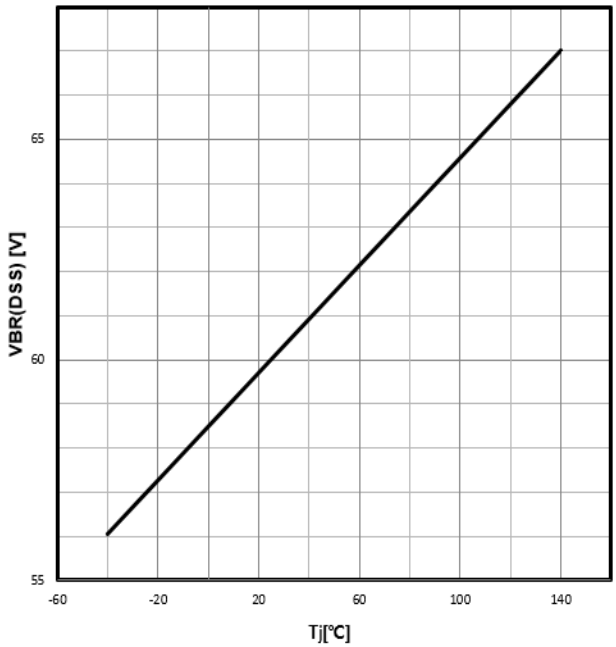
Drain-source on-state resistance
$R_{DS(on)}= f(T_j)$; I_D=-20A; V_{GS}=-10V



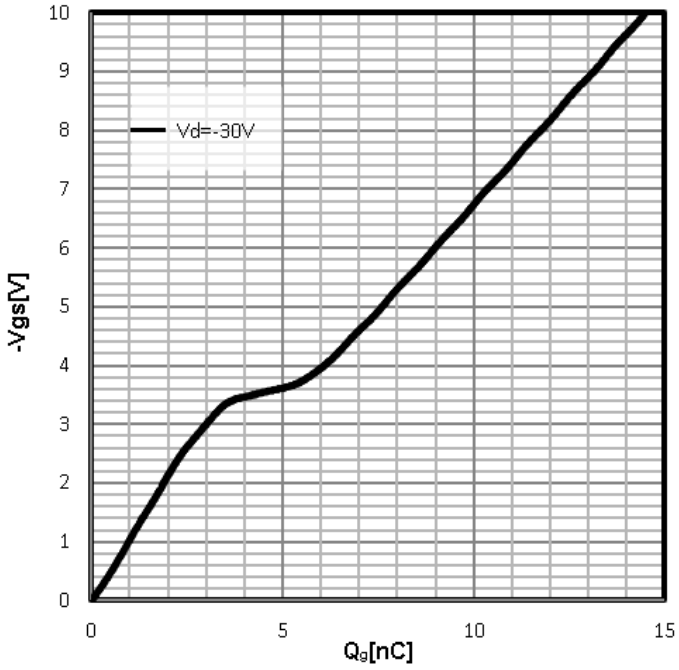
Gate Threshold Voltage
$-V_{TH}=f(T_j)$; I_D=-250uA



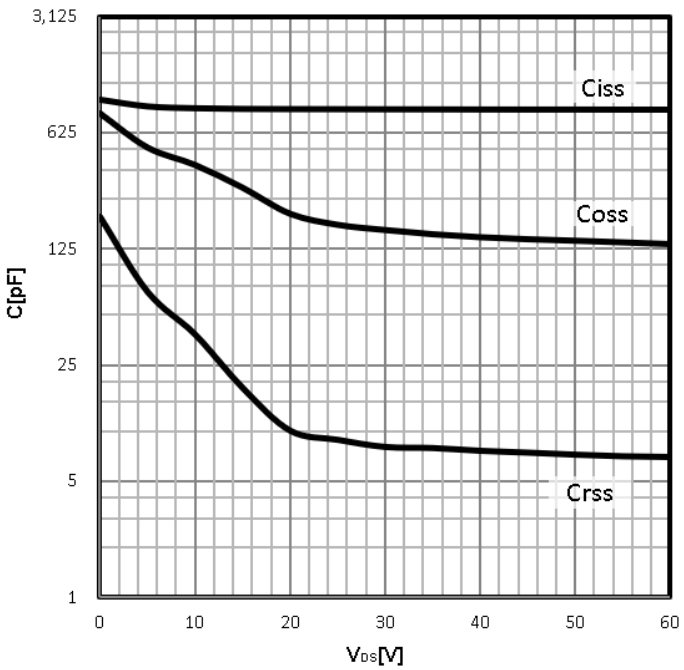
Drain-source breakdown voltage
$-V_{BR(DSS)}=f(T_j)$; I_D=-250uA



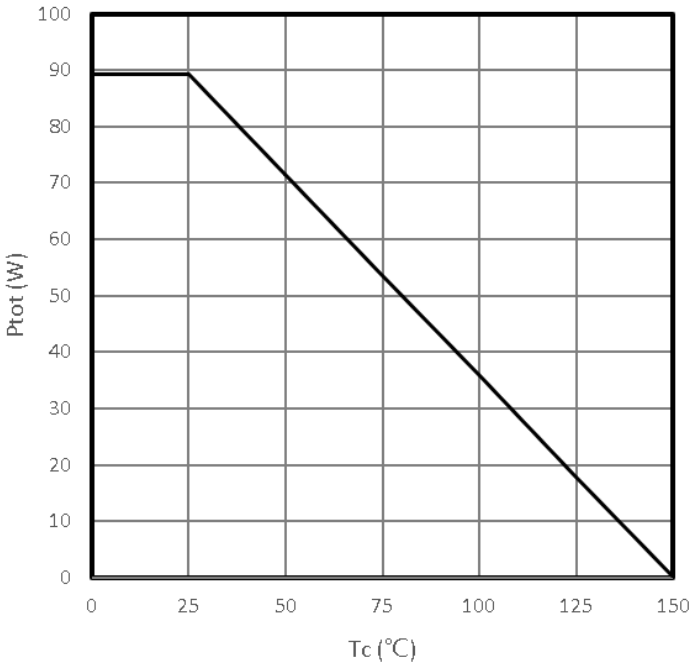
Typ. gate charge
$-V_{GS}=f(Q_g)$; I_D=-20A



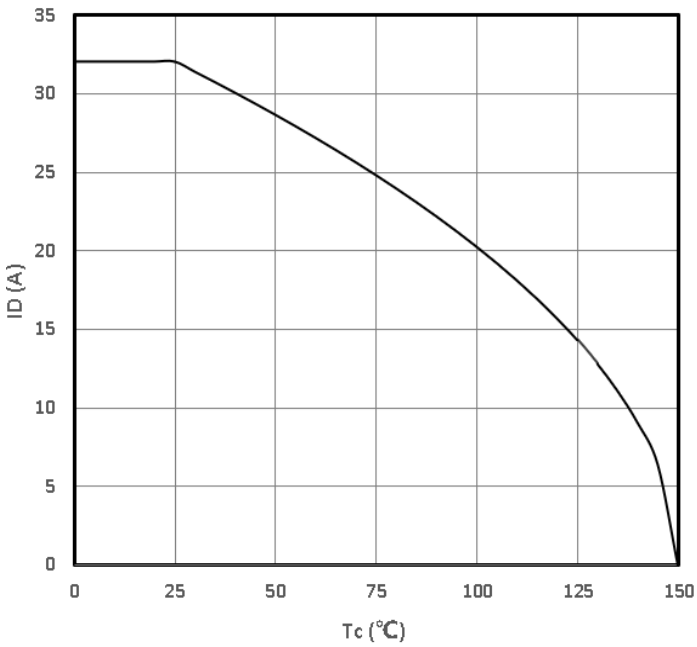
Typ. capacitances
C =f($-V_{DS}$); V_{GS}=0V; f =1MHz



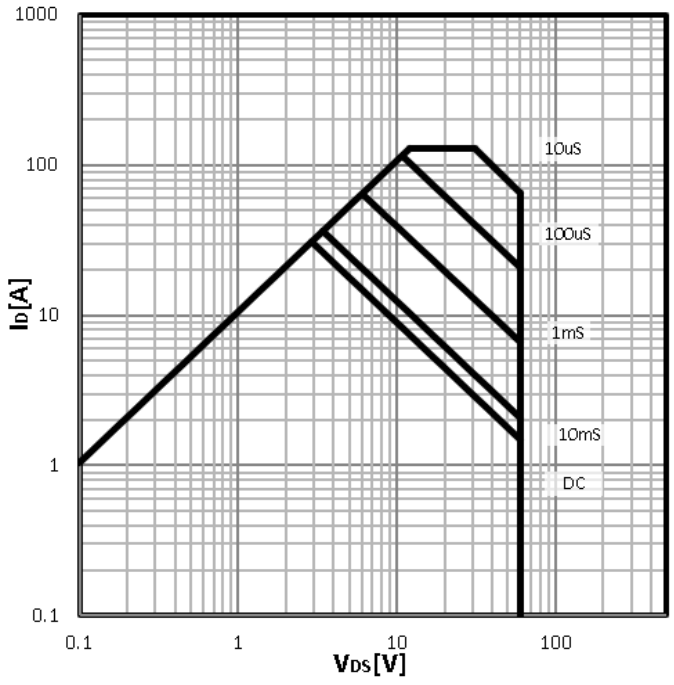
Power Dissipation
$P_{tot}=f(T_C)$



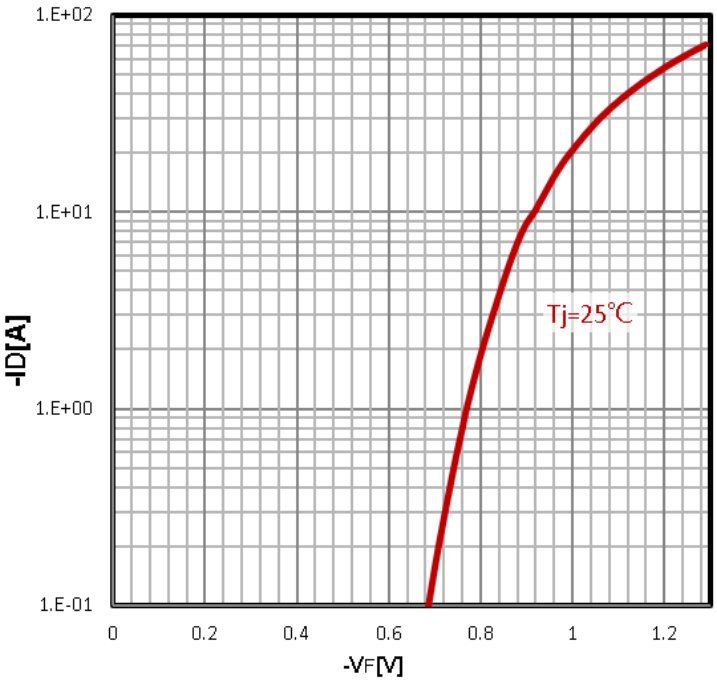
Maximum Drain Current
$-I_D=f(T_C)$



Safe operating area
$-I_D=f(-V_{DS})$

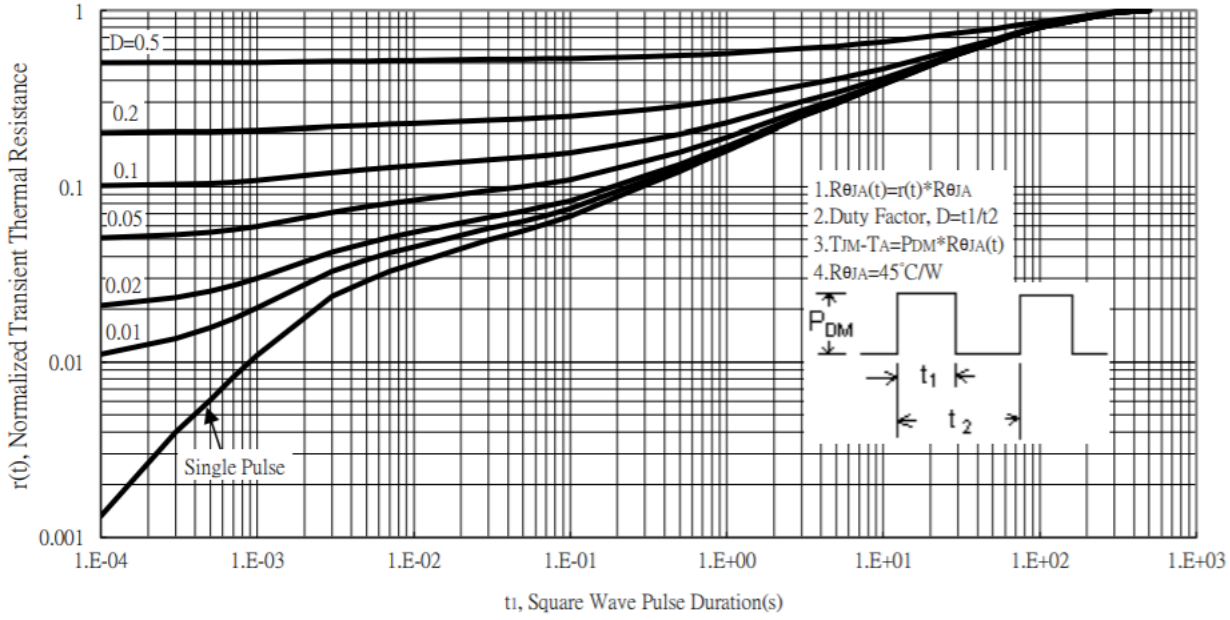


Body Diode Forward Voltage Variation
$-I_F=f(-V_{DS})$

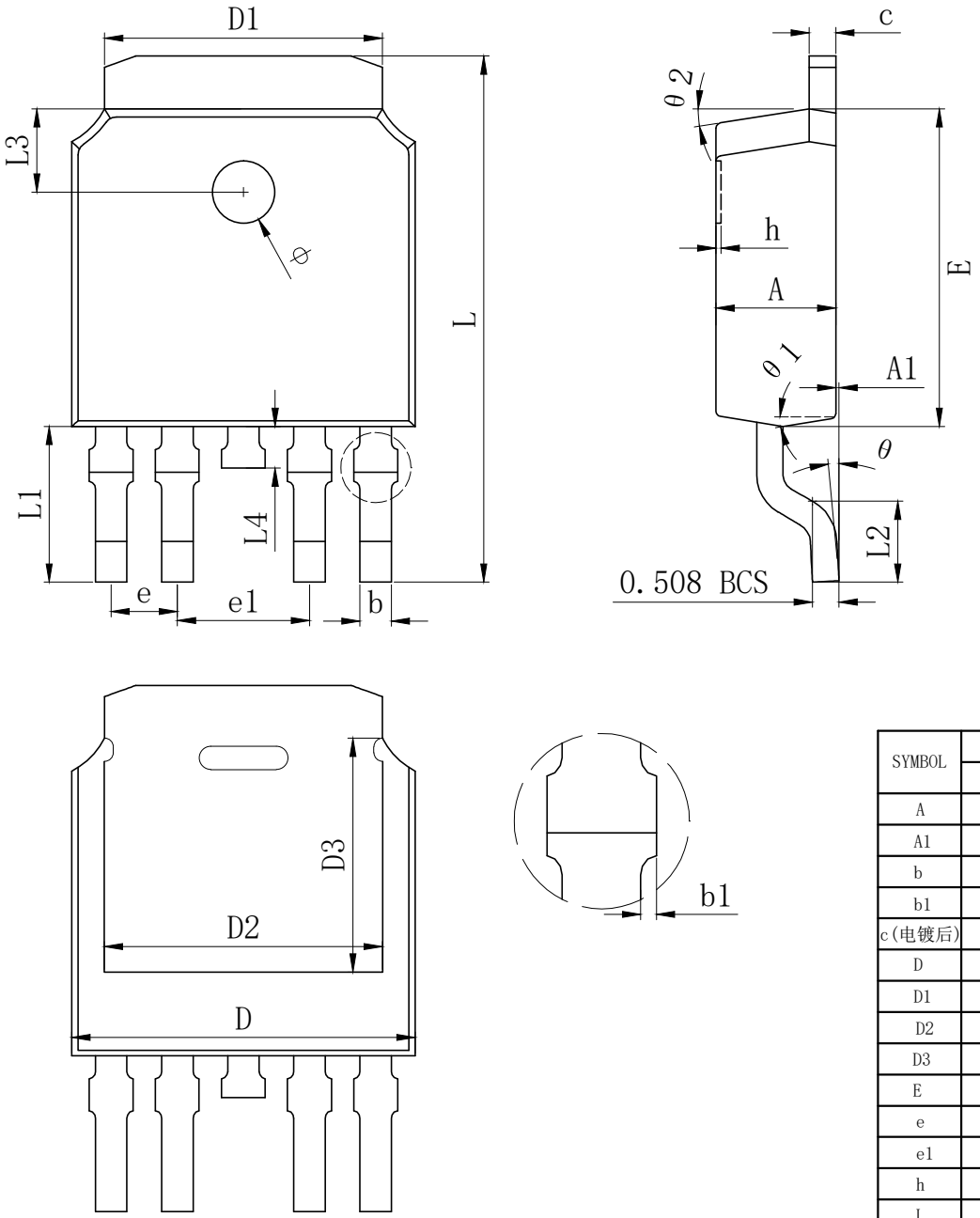


Max. transient thermal impedance

$Z_{thJC}=f(t_p)$



Mechanical Dimensions for TO-252-4L



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.550	0.600	0.650
b1	0.000		0.120
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	5.346 REF		
D3	4.490 REF		
E	6.000	6.100	6.200
e	1.270 TYP		
e1	2.540 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.988 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.700	0.800	0.900
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		